# Triple 750 MHz Voltage Feedback Op Amp with Enable Feature

NCS2540 is a triple 750 MHz voltage feedback monolithic operational amplifier featuring high slew rate and low differential gain and phase error. The voltage feedback architecture allows for a superior bandwidth and low power consumption. This device features an enable pin.

#### **Features**

- -3.0 dB Small Signal BW ( $A_V = +2.0, V_O = 0.5 V_{p-p}$ ) 750 MHz Typ
- Slew Rate 1700 V/us
- Supply Current 13 mA/amp
- Input Referred Voltage Noise  $5.0 \text{ nV}/\sqrt{\text{Hz}}$
- THD -64 dBc (f = 5.0 MHz,  $V_O = 2.0 V_{p-p}$ )
- Output Current 100 mA
- Enable Pin Available
- These are Pb-Free Devices

#### **Applications**

- Line Drivers
- Radar/Communication Receivers

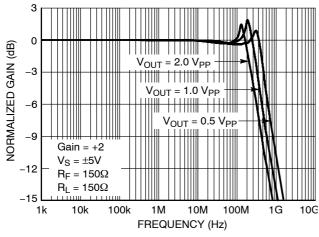


Figure 1. Frequency Response: Gain (dB) vs. Frequency Av = +2.0



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# MARKING DIAGRAM



TSSOP-16 DT SUFFIX CASE 948F



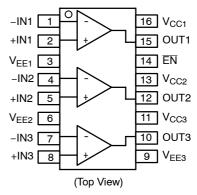
2540 = NCS2540

A = Assembly Location

L = Wafer Lot Y = Year W = Work Week • = Pb-Free Package

(Note: Microdot may be in either location)

#### **TSSOP-16 PINOUT**



#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NCS2540DTBG	TSSOP-16 (Pb-Free)	96 Units / Rail
NCS2540DTBR2G	TSSOP-16 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# PIN FUNCTION DESCRIPTION

Pin	Symbol	Function	Equivalent Circuit
10, 12, 15	OUTx	Output	V <sub>CC</sub> OUT OUT V <sub>EE</sub>
3, 6, 9	V <sub>EE</sub>	Negative Power Supply	
2, 5, 8	+INx	Non-inverted Input	V <sub>CC</sub> ESD  HIN  V <sub>EE</sub>
1, 4, 7	–INx	Inverted Input	See Above
11, 13, 16	V <sub>CC</sub>	Positive Power Supply	
14	EN	Enable	EN ESD VEE

# **ENABLE PIN TRUTH TABLE**

	High	Low*
Enable	Disabled	Enabled

\*Default open state

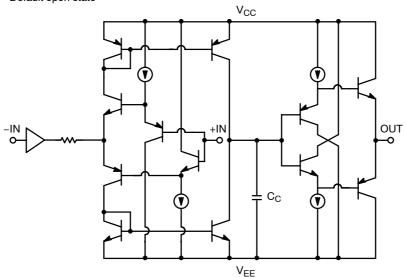


Figure 2. Simplified Device Schematic

#### **ATTRIBUTES**

Characteristics	Value
ESD Human Body Model Machine Model Charged Device Model	2.0 kV 200 V 1.0 kV
Moisture Sensitivity (Note 1)	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in

<sup>1.</sup> For additional information, see Application Note AND8003/D.

#### **MAXIMUM RATINGS**

Parameter	Symbol	Rating	Unit
Power Supply Voltage	V <sub>S</sub>	11	Vdc
Input Voltage Range	VI	≤V <sub>S</sub>	Vdc
Input Differential Voltage Range	V <sub>ID</sub>	≤V <sub>S</sub>	Vdc
Output Current	I <sub>O</sub>	100	mA
Maximum Junction Temperature (Note 2)	TJ	150	°C
Operating Ambient Temperature	T <sub>A</sub>	-40 to +85	°C
Storage Temperature Range	T <sub>stg</sub>	-60 to +150	°C
Power Dissipation	P <sub>D</sub>	(See Graph)	mW
Thermal Resistance, Junction-to-Air	$R_{ heta JA}$	179	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

# **MAXIMUM POWER DISSIPATION**

The maximum power that can be safely dissipated is limited by the associated rise in junction temperature. For the plastic packages, the maximum safe junction temperature is 150°C. If the maximum is exceeded momentarily, proper circuit operation will be restored as soon as the die temperature is reduced. Leaving the device in the "overheated" condition for an extended period can result in device damage.

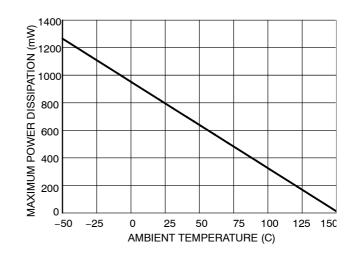


Figure 3. Power Dissipation vs. Temperature

<sup>2.</sup> Power dissipation must be considered to ensure maximum junction temperature (T<sub>J</sub>) is not exceeded.

**AC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +5.0 V,  $V_{EE}$  = -5.0 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUENC	CY DOMAIN PERFORMANCE					
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$A_V = +2.0, V_O = 0.5 V_{p-p}$ $A_V = +2.0, V_O = 2.0 V_{p-p}$		750 350		MHz
GF <sub>0.1dB</sub>	0.1 dB Gain Flatness Bandwidth	A <sub>V</sub> = +2.0		40		MHz
dG	Differential Gain	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.07		%
dΡ	Differential Phase	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.01		0
TIME DOM	AIN RESPONSE					
SR	Slew Rate	$A_V = +2.0, V_{step} = 2.0 V$		1700		V/μs
t <sub>s</sub>	Settling Time 0.1%	A <sub>V</sub> = +2.0, V <sub>step</sub> = 2.0 V		10		ns
t <sub>r</sub> t <sub>f</sub>	Rise and Fall Time	$(10\%-90\%) A_V = +2.0, V_{step} = 2.0 V$		2.0		ns
t <sub>ON</sub>	Turn-on Time			20		ns
t <sub>OFF</sub>	Turn-off Time			40		ns
HARMONIC	NOISE PERFORMANCE					
THD	Total Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-64		dB
HD2	2nd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-65		dBc
HD3	3rd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		-75		dBc
IP3	Third-Order Intercept	$f = 10 \text{ MHz}, V_O = 1.0 V_{p-p}$		40		dBm
SFDR	Spurious-Free Dynamic Range	$f = 5.0 \text{ MHz}, V_O = 2.0 V_{p-p}$		65		dBc
e <sub>N</sub>	Input Referred Voltage Noise	f = 1.0 MHz		5.0		nV/√H
i <sub>N</sub>	Input Referred Current Noise	f = 1.0 MHz		4.0		pA/√Hz

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +5.0 V,  $V_{EE}$  = -5.0 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
DC PERFO	RMANCE		•	•		•
V <sub>IO</sub>	Input Offset Voltage (Note 3)		-10	0	+10	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I <sub>IB</sub>	Input Bias Current	V <sub>O</sub> = 0 V		±3.2	±20	μΑ
$\Delta I_{\text{IB}}/\Delta T$	Input Bias Current Temperature Coefficient	V <sub>O</sub> = 0 V		±40		nA/°C
V <sub>IH</sub>	Input High Voltage (Enable) (Note 3)		3.0			V
V <sub>IL</sub>	Input Low Voltage (Enable) (Note 3)				1.0	V
INPUT CHA	RACTERISTICS					
$V_{CM}$	Input Common Mode Voltage Range (Note 3)		±3.0	±3.2		V
CMRR	Common Mode Rejection Ratio (Note 3)	(See Graph)	40	50		dB
R <sub>IN</sub>	Input Resistance			4.5		МΩ
C <sub>IN</sub>	Differential Input Capacitance			1.0		pF
OUTPUT CI	HARACTERISTICS					
R <sub>OUT</sub>	Output Resistance			0.1		Ω
Vo	Output Voltage Range		±3.0	±4.0		V
ΙO	Output Current		±50	± 100		mA
POWER SU	IPPLY					
V <sub>S</sub>	Operating Voltage Supply			10		V
I <sub>S,ON</sub>	Power Supply Current – Enabled per amplifier (Note 3)		5.0	13	17	mA
I <sub>S,OFF</sub>	Power Supply Current – Disabled per amplifier			0.1	0.3	mA
PSRR	Power Supply Rejection Ratio (Note 3)	(See Graph)	40	56		dB
	Crosstalk	Channel to Channel, f = 5 MHz		85		dB

<sup>3.</sup> Guaranteed by design and/or characterization.

**AC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +2.5 V,  $V_{EE}$  = -2.5 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
FREQUENC	CY DOMAIN PERFORMANCE					
BW	Bandwidth 3.0 dB Small Signal 3.0 dB Large Signal	$A_V = +2.0, V_O = 0.5 V_{p-p}$ $A_V = +2.0, V_O = 1.0 V_{p-p}$		550 200		MHz
GF <sub>0.1dB</sub>	0.1 dB Gain Flatness Bandwidth	A <sub>V</sub> = +2.0		35		MHz
dG	Differential Gain	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.07		%
dΡ	Differential Phase	$A_V = +2.0, R_L = 150 \Omega, f = 3.58 MHz$		0.02		0
TIME DOM	AIN RESPONSE					
SR	Slew Rate	A <sub>V</sub> = +2.0, V <sub>step</sub> = 1.0 V		900		V/μs
t <sub>s</sub>	Settling Time 0.1%	A <sub>V</sub> = +2.0, V <sub>step</sub> = 1.0 V		10		ns
t <sub>r</sub> t <sub>f</sub>	Rise and Fall Time	$(10\%-90\%) A_V = +2.0, V_{step} = 1.0 V$		1.7		ns
t <sub>ON</sub>	Turn-on Time			20		ns
t <sub>OFF</sub>	Turn-off Time			40		ns
HARMONIC	NOISE PERFORMANCE					
THD	Total Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-60		dB
HD2	2nd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-65		dBc
HD3	3rd Harmonic Distortion	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		-63		dBc
IP3	Third-Order Intercept	$f = 10 \text{ MHz}, V_O = 0.5 V_{p-p}$		35		dBm
SFDR	Spurious-Free Dynamic Range	$f = 5.0 \text{ MHz}, V_O = 1.0 V_{p-p}$		63		dBc
e <sub>N</sub>	Input Referred Voltage Noise	f = 1.0 MHz		5.0		nV/√H:
i <sub>N</sub>	Input Referred Current Noise	f = 1.0 MHz		4.0		pA/√Hz

**DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = +2.5 V,  $V_{EE}$  = -2.5 V,  $T_A$  = -40°C to +85°C,  $R_L$  = 150  $\Omega$  to GND,  $R_F$  = 150  $\Omega$ ,  $A_V$  = +2.0, Enable is left open, unless otherwise specified).

Symbol	Characteristic	Conditions	Min	Тур	Max	Unit
DC PERFO	RMANCE		•			•
V <sub>IO</sub>	Input Offset Voltage (Note 4)		-10	0	+10	mV
$\Delta V_{IO}/\Delta T$	Input Offset Voltage Temperature Coefficient			6.0		μV/°C
I <sub>IB</sub>	Input Bias Current	V <sub>O</sub> = 0 V		±3.2	±20	μΑ
$\Delta I_{IB}/\Delta T$	Input Bias Current Temperature Coefficient	V <sub>O</sub> = 0 V		±40		nA/°C
V <sub>IH</sub>	Input High Voltage (Enable) (Note 4)		1.5			V
$V_{IL}$	Input Low Voltage (Enable) (Note 4)				0.5	V
NPUT CHA	RACTERISTICS					
V <sub>CM</sub>	Input Common Mode Voltage Range (Note 4)		±1.1	±1.5		V
CMRR	Common Mode Rejection Ratio (Note 4)	(See Graph)	40	50		dB
R <sub>IN</sub>	Input Resistance			4.5		МΩ
C <sub>IN</sub>	Differential Input Capacitance			1.0		pF
OUTPUT C	HARACTERISTICS		•			•
R <sub>OUT</sub>	Output Resistance			0.1		Ω
Vo	Output Voltage Range		±1.1	±1.5		V
Ιο	Output Current		±50	±100		mA
POWER SU	IPPLY					
Vs	Operating Voltage Supply			5.0		V
I <sub>S,ON</sub>	Power Supply Current – Enabled per amplifier		5.0	11	17	mA
I <sub>S,OFF</sub>	Power Supply Current – Disabled per amplifier			0.1	0.3	mA
PSRR	Power Supply Rejection Ratio (Note 4)	(See Graph)	40	56		dB
	Crosstalk	Channel to Channel, f = 5 MHz		85		dB

<sup>4.</sup> Guaranteed by design and/or characterization.

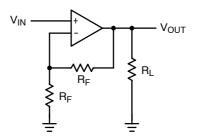


Figure 4. Typical Test Setup (A<sub>V</sub> = +2.0, R<sub>F</sub> = 150 k $\Omega$ , R<sub>L</sub> = 150  $\Omega$ )

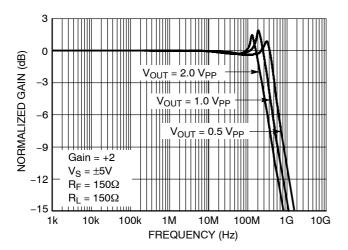


Figure 5. Frequency Response: Gain (dB) vs. Frequency Av = +2.0

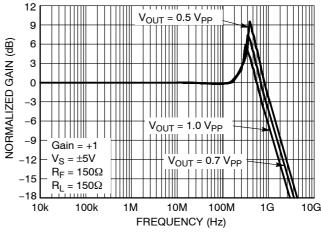


Figure 6. Frequency Response: Gain (dB) vs. Frequency Av = +1.0

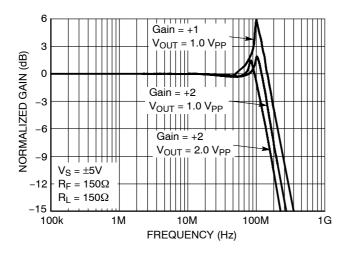


Figure 7. Large Signal Frequency Response Gain (dB) vs. Frequency

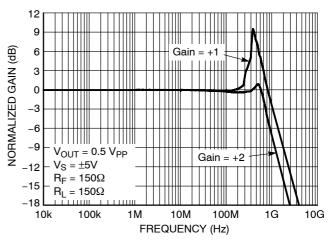


Figure 8. Small Signal Frequency Response Gain (dB) vs. Frequency

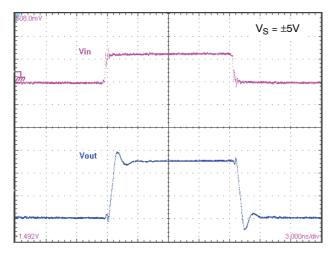


Figure 9. Small Signal Step Response Vertical: 20 mV/div Horizontal: 3 ns/div

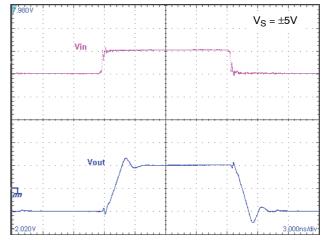
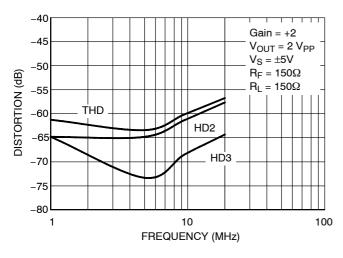


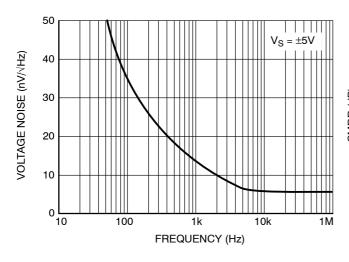
Figure 10. Large Signal Step Response Vertical: 1 V/div Horizontal: 3 ns/div



-40 Gain = +2-45 Freq = 5 MHz  $V_S = \pm 5V$ -50  $R_F=150\Omega\,$ DISTORTION (dB)  $R_L = 150\Omega$ -55 -60 THD -65 HD2 -70 HD3 -75 -80 0 0.5 1.5 2 2.5 3 3.5 4.5  $V_{OUT}$  ( $V_{PP}$ )

Figure 11. THD, HD2, HD3 vs. Frequency

Figure 12. THD, HD2, HD3 vs. Output Voltage



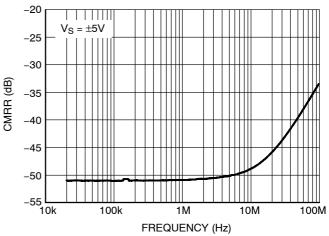
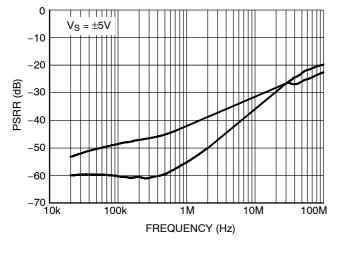


Figure 13. Input Referred Voltage Noise vs. Frequency

Figure 14. CMRR vs. Frequency



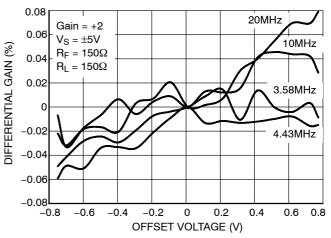


Figure 15. PSRR vs. Frequency

Figure 16. Differential Gain

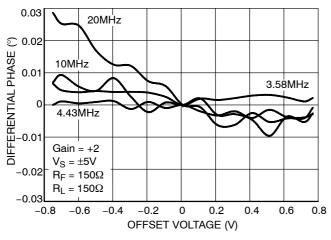


Figure 17. Differential Phase

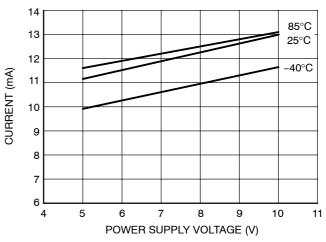


Figure 18. Supply Current Per Amplifier vs. Power Supply (Enabled)

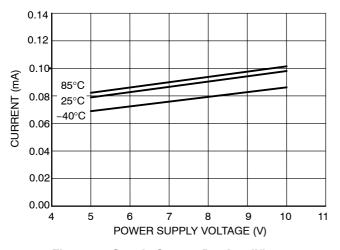


Figure 19. Supply Current Per Amplifier vs. Temperature (Disabled)

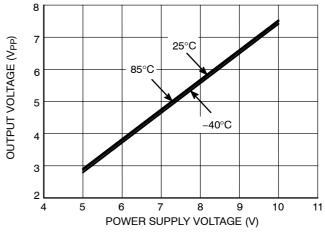


Figure 20. Output Voltage Swing vs. Supply Voltage

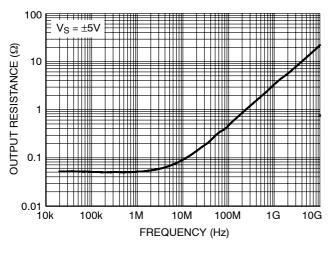


Figure 21. Output Resistance vs. Frequency

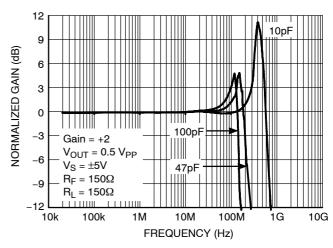


Figure 22. Frequency Response vs. Capacitive Load

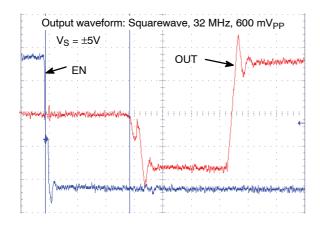


Figure 23. Turn ON Time Delay Vertical: 500 mV/div (Enable), 200 mV/div (Output) Horizontal: 5 ns/div

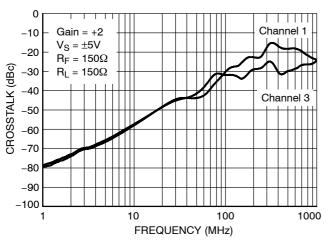


Figure 25. Crosstalk vs Frequency (Crosstalk measured on Channel 2 with input signal on Channel 1 and 3)

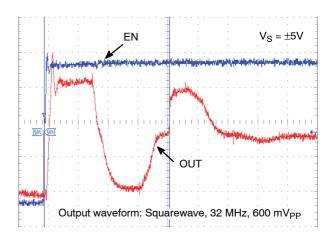


Figure 24. Turn OFF Time Delay Vertical: 500 mV/div (Enable), 200 mV/div (Output) Horizontal: 10 ns/div

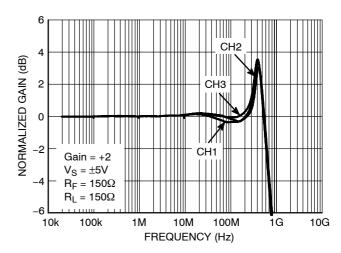


Figure 26. Channel Matching (dB) vs Frequency

# **Printed Circuit Board Layout Techniques**

Proper high speed PCB design rules should be used for all wideband amplifiers as the PCB parasitics can affect the overall performance. Most important are stray capacitances at the output and inverting input nodes as it can effect peaking and bandwidth. A space (3/16" is plenty) should be left around the signal lines to minimize coupling. Also, signal lines connecting the feedback and gain resistors should be short enough so that their associated inductance does not cause high frequency gain errors. Line lengths less than 1/4" are recommended.

#### Video Performance

This device designed to provide good performance with NTSC, PAL, and HDTV video signals. Best performance is obtained with back terminated loads as performance is degraded as the load is increased. The back termination reduces reflections from the transmission line and effectively masks transmission line and other parasitic capacitances from the amplifier output stage.

#### **ESD Protection**

All device pins have limited ESD protection using internal diodes to power supplies as specified in the attributes table (see Figure 27). These diodes provide moderate protection

to input overdrive voltages above the supplies. The ESD diodes can support high input currents with current limiting series resistors. Keep these resistor values as low as possible since high values degrade both noise performance and frequency response. Under closed–loop operation, the ESD diodes have no effect on circuit performance. However, under certain conditions the ESD diodes will be evident. If the device is driven into a slewing condition, the ESD diodes will clamp large differential voltages until the feedback loop restores closed–loop operation. Also, if the device is powered down and a large input signal is applied, the ESD diodes will conduct.

NOTE: Human Body Model for +IN and –IN pins are rated at 0.8kV while all other pins are rated at 2.0kV.

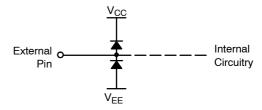
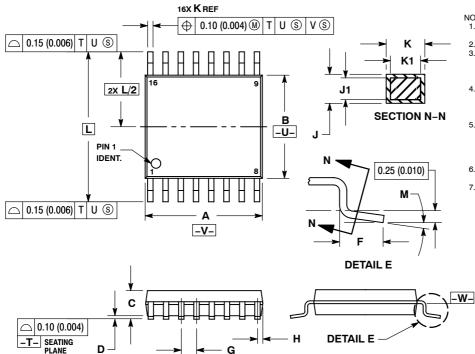


Figure 27. Internal ESD Protection

#### PACKAGE DIMENSIONS

# TSSOP-16 CASE 948F-01 **ISSUE B**

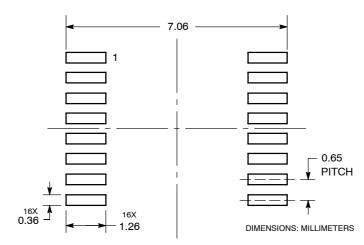


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

- CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD FLASH OR GATE BURRS SHALL NOT
  EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
  INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
  DIMENSION K DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.08 (0.003) TOTAL
  IN EXCESS OF THE K DIMENSION AT
  MAXIMUM MATERIAL CONDITION.
  TERMINAL NUMBERS ARE SHOWN FOR
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0°	8°	0°	8°	

# **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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